onsemi

N-Channel Enhancement Mode Field Effect Transistor 2N7002T

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- This Device is Pb–Free and are RoHS Compliant

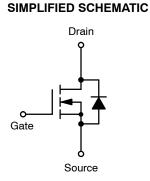
Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V _{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \leq 1.0~M\Omega$	V _{DGR}	60	V	
Gate–Source Voltage Continuous Pulsed	V _{GSS}	±20 ±40	V	
Gate–Source Voltage Continuous Continuous at 100°C Pulsed	Ι _D	115 73 800	mA	
Junction Temperature Range	TJ	150	°C	
Storage Temperature Range	T _{STG}	–55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS (T_A = 25° C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

		,		
Parameter	Symbol	Max	Unit	
Total Device Dissipation Derating above T _A = 25°C	P _D	200 1.6	mW mW/°C	
Thermal Resistance, Junction-to-Ambient (Note 1)	R_{\thetaJA}	625	°C/W	

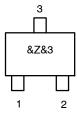
1. Device mounted on FR–4 PCB, 1 inch \times 0.85 inch \times 0.062 inch. Minimum land pad size.





SOT-523FL CASE 419BG

MARKING DIAGRAM



&Z = Assembly location &3 = Data code

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7002T	SOT–523FL (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

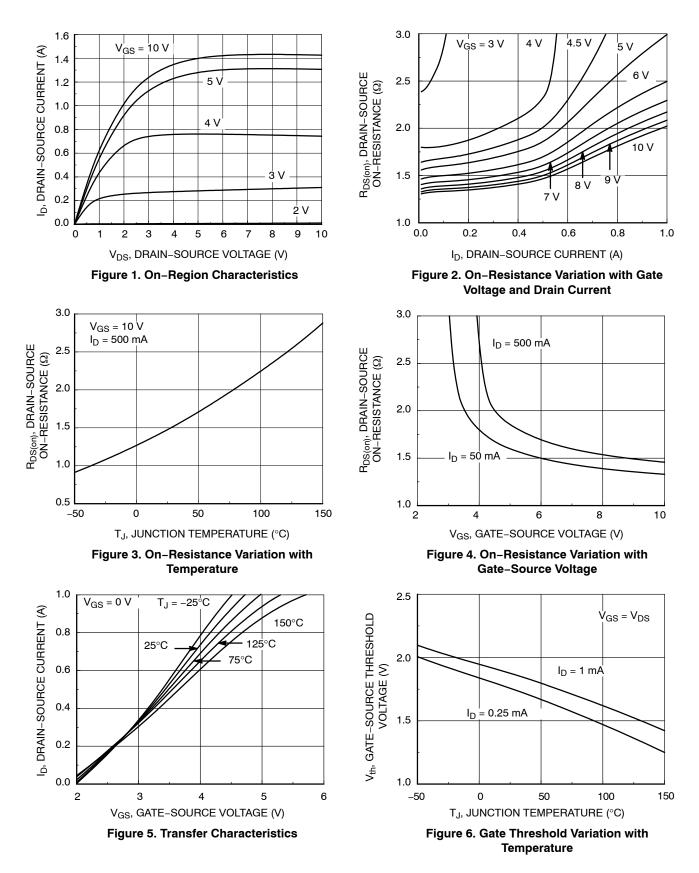
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Parameter	Symbol	Test Condition	Min	Тур	Max	Units
OFF CHARACTERISTICS (Note 2)						-
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} = 0 V, I_D = 10 μ A	60	78	-	V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	-	0.001	1.0	μΑ
		$V_{GS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $T_J = 125^{\circ}\text{C}$	-	7	500	μΑ
Gate-Body Leakage Current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	-	0.2	±10	nA
ON CHARACTERISTICS (Note 2)	•		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0	1.76	2.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 5 V, I _D = 0.05 A	-	1.6	7.5	Ω
		V _{GS} = 10 V, I _D = 0.5 A	-	-	2.0	Ω
		V_{GS} = 10 V, I _D = 0.5 A, T _J = 125°C	-	2.53	13.5	Ω
On-State Drain Current	I _{D(ON)}	V_{GS} = 10 V, V_{DS} = 7.5 V	0.5	1.43	-	А
Forward Transconductance	9FS	V_{DS} = 10 V, I_{D} = 0.2 A	80	356.5	-	mS
DYNAMIC CHARACTERISTICS			•			
Input Capacitance	C _{ISS}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, $ f = 1.0 MHz	-	37.8	50	pF
Output Capacitance	C _{OSS}		-	12.4	25	
Reverse Transfer Capacitance	C _{RSS}		-	6.5	7.0	
SWITCHING CHARACTERISTICS	•		•	•		•
Turn-On Delay Time	t _{D(ON)}	$V_{DD} = 30$ V, $I_D = 0.2$ A, $V_{GEN} = 10$ V, $R_L = 150$ Ω, $R_{GEN} = 25$ Ω	-	5.85	20	ns
Turn-Off Delay Time	t _{D(OFF)}		_	12.5	20	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Short duration test pulse used to minimize self-heating effect.

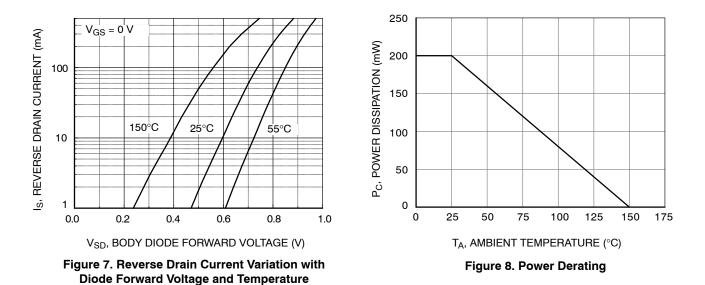
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TYPICAL PERFORMANCE CHARACTERISTICS



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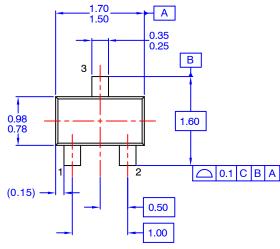
TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)



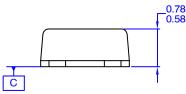
ON

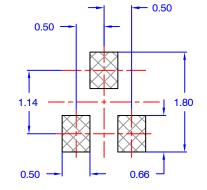
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DATE 29 SEP 2017

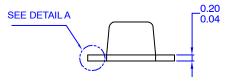


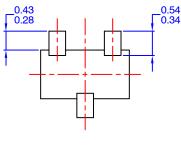




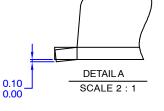


LAND PATTERN RECOMMENDATION





BOTTOM VIEW



NOTES:

- A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS,
- MOLD FLASH, AND TIE BAR EXTRUSIONS.

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